

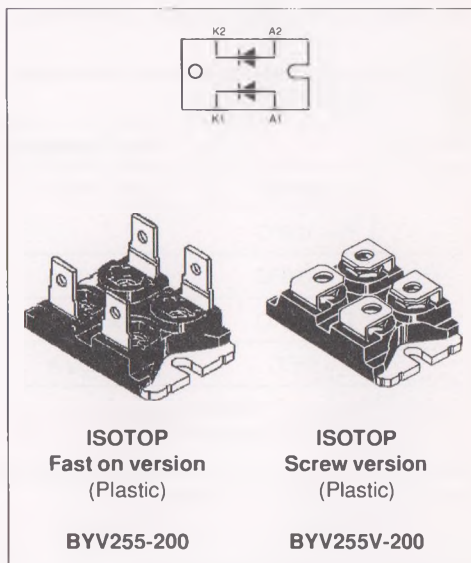
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED :
 Insulating voltage = 2500 V_{RMS}
 Capacitance = 55 pF

DESCRIPTION

Dual rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in ISOTOP™ this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
I _{F(RMS)}	RMS forward current		Per diode	150	A
I _{F(AV)}	Average forward current $\delta = 0.5$	T _C =110°C	Per diode	100	A
I _{FSM}	Surge non repetitive forward current	t _p =10ms sinusoidal	Per diode	1600	A
T _{stg} T _j	Storage and junction temperature range			- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	BYV255-(V)				Unit
		50	100	150	200	
V _{RRM}	Repetitive peak reverse voltage	50	100	150	200	V

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THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	Per diode	0.4	°C/W
		Total	0.25	
Rth (c)	Coupling		0.1	°C/W

When the diodes 1 and 2 are used simultaneously :
 $T_j - T_c$ (diode 1) = P(diode 1) x Rth(j-c)(Per diode) + P(diode 2) x Rth(c)

ELECTRICAL CHARACTERISTICS (Per diode)
STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			100	μA
	T _j = 100°C				10	mA
V _F **	T _j = 125°C	I _F = 100 A			0.85	V
	T _j = 125°C	I _F = 200 A			1.00	
	T _j = 25°C	I _F = 200 A			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.7 \times I_{F(AV)} + 0.0015 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
trr	T _j = 25°C	I _F = 0.5A I _R = 1A	I _{rr} = 0.25A			55	ns
		I _F = 1A V _R = 30V	diF/dt = -50A/μs			80	
tfr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 x V _F	tr = 5 ns		10	ns	
V _{FP}	T _j = 25°C	I _F = 1A	tr = 5 ns		1.5	V	

TURN-OFF SWITCHING CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
I _{RM}	T _j = 100°C	I _F = 100A Lp ≤ 0.05μH V _{CC} ≤ 0.6 V _{RRM}	diF/dt = -200A/μs			16	A
			diF/dt = -400A/μs		24		

Fig.1 : Average forward power dissipation versus average forward current.

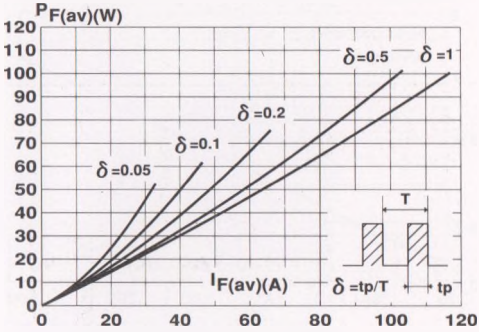


Fig.2 : Peak current versus form factor.

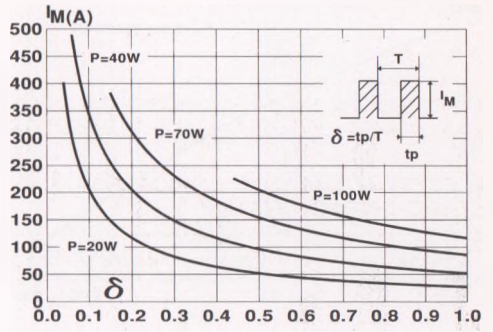


Fig.3 : Forward voltage drop versus forward current (maximum values).

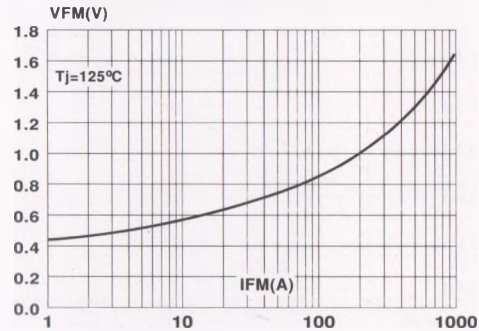


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

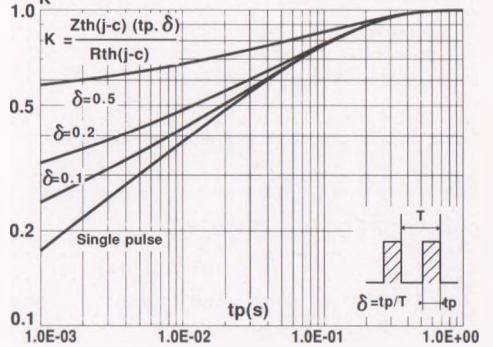


Fig.5 : Non repetitive surge peak forward current versus overload duration.

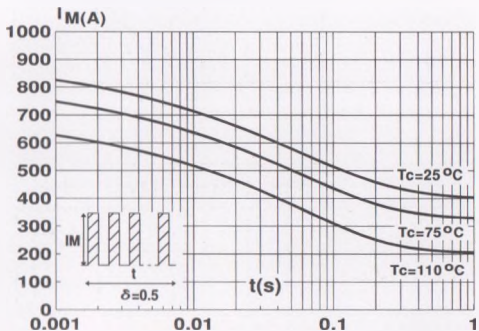


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)

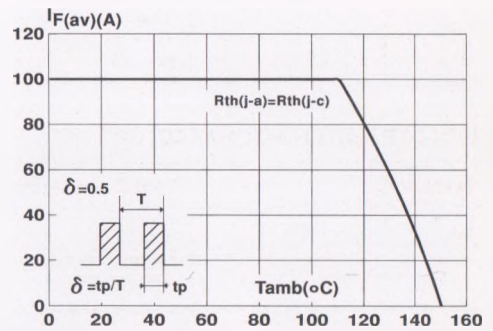


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

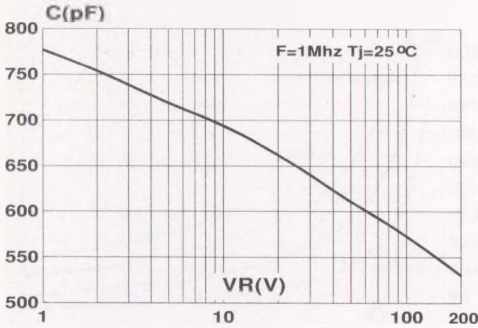


Fig.8 : Recovery charges versus dI_F/dt .

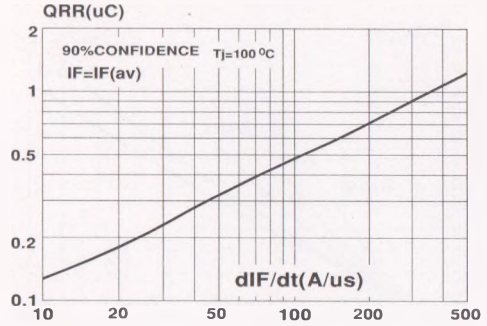


Fig.9 : Peak reverse current versus dI_F/dt .

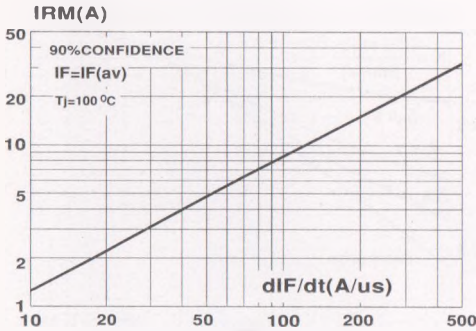


Fig.10 : Dynamic parameters versus junction temperature.

